

POSTER SESSION B Tuesday, May 18 19⁰⁰ - 21⁰⁰

- B 1 PHOTOREFLECTANCE OF THICK GAN LAYERS GROWN BY HVPE** R. Kudrawiec, R. Korbutowicz, R. Paszkiewicz, M. Syperek, J. Misiewicz, *The Faculty of Microsystem Electronics and Photonics, Wrocław University of Technology, Wrocław, Poland*
- B 2 X-RAY CHARACTERIZATION OF THICK GAN LAYERS GROWN BY HVPE** R. Korbutowicz, J. Kozłowski, E. Dumiszewska, J. Serafińczuk *The Faculty of Microsystem Electronics and Photonics, Wrocław University of Technology, Poland*
- B 3 HYDRIDE VAPOR PHASE EPITAXY (HVPE) GROWTH OF GAN LAYERS** Bolesław Łuczniak, Izabella Grzegory, Grzegorz Nowak, Grzegorz Kamler, Jolanta Borysiuk, Marcin Kryśko, Michał Leszczyński, Stanisław Krukowski, Filip Tuomisto*, Michał Boćkowski, *Sylwester Porowski High Pressure Research Center Polish Academy of Sciences, Warsaw, Poland*
- B 4 STRESS-INDUCED SEPARATION OF RECOMBINING CARRIERS IN NITRIDE GaN/(AlGa)N QUANTUM WELLS** J. Galczak, R. P. Sarzała and W. Nakwaski *Laboratory of Computer Physics, Institute of Physics, Technical University of Łódź*
- B 5 THE SELF-CONSISTENT MODEL OF THE 1.3- μm OXIDE-CONFINED EDGE-EMITTING QUANTUM-DOT (InGa)As/GaAs DIODE LASERS** R. P. Sarzała, M. Wasiak, T. Czyszanowski, and W. Nakwaski, *Laboratory of Computer Physics, Institute of Physics, Technical University of Łódź*
- B 6 THE EFFECT OF SULPHUR PASSIVATION TREATMENT ON GaSb/InGaAsSb/AlGaAsSb PHOTOVOLTAIC DETECTOR PARAMETERS** K. Golaszewska, E. Papis, A. Piotrowska, T.T. Piotrowski, E. Kamińska, R. Kruska, R. Lukaszewicz, J. Rutkowski, J. Szade, A. Winiarski, A. Wawro *Institute of Electron Technology, Warsaw, Poland*
- B 7 FABRICATION OF OHMIC INDIUM CONTACTS ON SEMIINSULATING GaAs BY LASER DEPOSITION AND PROCESSING** V. Kazlauskienė, V. Kažukauskas, J. Miškinis, A. Petravičius, R. Pūras, S. Sakalauskas, J. Sinius, J.-V. Vaitkus, A. Žindulis *Institute of Materials Science and Applied Research,*
- B 8 PHOTOLUMINESCENCE AND CHARACTERIZATION OF THE GaAs QUASI- DELTA-DOPED SUPERLATTICES** B.N. Zvonkov, S.V. Morozov, V.I. Gavrilenko, V.K. Kononenko, D.V. Ushakov *Stepanov Institute of Physics NASB, Belarus*
- B 9 EARLY STAGES OF LOW TEMPERATURE EPITAXIAL GROWTH OF InSb ON GaAs** A. Borowska, R. Cajka, M. Oszwałdowski and A Richter, *Instytut Fizyki, Politechnika Poznańska, Poznań, Poland*
- B 10 OPTICAL PROPERTIES OF InP LAYERS PREPARED WITH THE ADDITION OF Ce, Tm AND Lu IN THE GROWTH MELT** J. Zavadil and O. Procházková, *Institute of Radio Engineering and Electronics, Academy of Sciences of the Czech Republic*
- B 11 EVOLUTION OF STRESS AND STRUCTURE IN CU THIN FILMS:IN-SITU EXPERIMENT** D.Chocyk, A.Proszynski, T. Pienkos, L. Gladyszewski, T. Zientarski and G.Gladyszewski, *Maria Curie-Skłodowska University Lublin, Poland,*
- B 12 EVOLUTION OF STRESS AND STRUCTURE IN CU THIN FILMS: MOLECULAR DYNAMICS SIMULATION.** T. Zientarski, D. Chocyk *Department for the Modelling of Physico-Chemical Processes, Maria Curie-Skłodowska University Lublin, Poland,*
- B 13 CHARACTERISTICS OF MULTI-LAYER SINGLE CRYSTAL THIN FILMS ON THE LiNbO₃ SUBSTRATE BY LPE METHOD** H.J. Lee, T.I. Shin, S. G. Yoon, and D.H. Yoon *Department of Advanced Materials Engineering, Sungkyunkwan University, Suwon 440- 746, Korea*
- B 14 LINEAR AND NONLINEAR OPTICAL PROPERTIES Zn_{1-x}Mg_xSe LAYERS GROWN BY MBE AND LPD METHOD** B. Derkowska, M. Wojdyła, P. Płociennik, B. Sahraoui and W. Bała *Institute of Physics, N. Copernicus University, Toruń, Poland*
- B 15 PRESSURE AND MAGNETIC FIELD EFFECTS ON RESISTANCE AND MAGNETORESISTANCE IN (La_{0.7}Ca_{0.3})_{1-x}Mn_{1+x}O_{3- δ}** V.P. Dyakonov, V. Mikhaylov, E.Zubov, A.V. Pashchenko, A.Szewczyk, K. Piotrowski, H. Szymczak and K. Dyakonov *Institute of Physics, PAS, Warsaw, Poland.*
- B 16 ACOUSTO - ELECTRICAL EFFECTS IN THE La_{0.67}Ca_{0.33}MnO₃ FILM** V.P. Dyakonov, A. Abal'oshev, P. Gierłowski, S. J. Lewandowski, Szymczak, K. Dyakonov and A. Goltsev, *Institute of Physics, Polish Academy of Sciences, 02-668 Warszawa, Poland*
- B 17 PREPARATION OF UNDOPED AND INDIUM DOPED ZnO THIN FILMS BY PULSED LASER DEPOSITION METHOD** B.Kotlyarchuk, V.Savchuk, M.Oszwałdowski *Pidstryhach Institute for Applied problems of Mechanics and Mathematics, Lviv, Ukraine*
- B 18 PROPERTIES OF ZrN FILMS AS SUBSTRATE MASKS IN LIQUID PHASE EPITAXIAL LATERAL OVERGROWTH OF COMPOUND SEMICONDUCTOR** D. Dobosz, Z.R. Zytewicz, E. Kamińska, A. Piotrowska, K. Golaszewska, T.T. Piotrowski *Institute of Physics, Polish Academy of Sciences, Warszawa,*
- B 19 CHANGE OF DLC:H AND A-SIC:H LAYERS PROPERTIES AFTER THERMAL TREATMENT** J.Gurovič, F. Černý, M. Solar, P. Matějka, D. Palamarchuk *Faculty of Mechanical Engineering CTU Prague, Praha 6*
- B 20 STUDIES ON SPONTANEOUS FORMATION OF 1D NANOCRYSTALS OF SILICON CARBIDE** A.Huczko, H.Lange, M. Bystrzejewski and S. Cudziło *Department of Chemistry, Warsaw University, 02092 Warsaw, Poland*
- B 21 STUDY OF PHOTOVOLTAGE IN CuPc THIN FILMS** Bratkowski, P. Borowski, W. Bała, A. Korcala, Z. Łukasiak *Institute of Physics, N. Copernicus University, Toruń, Poland*

- B 22 STUDY OF VACUUM DEPOSITED CuPc THIN FILMS BY FT-IR AND RAMAN SCATTERING SPECTROSCOPY**
W. Bała, A. Grodzicki, P. Piszczek, M. Wojdyła, A. Bratkowski, T. Runka, M. Szybowski, M. Drozdowski, *Faculty of Technical Physics,, Poznan University of Technology, Poznan, Poland*
- B 23 PHOTOLUMINESCENCE CHARACTERIZATION OF VACUUM DEPOSITED PTCDA THIN FILMS**
W. Bała, Z. Łukasiak, M. Rebarz, P. Dalasiński, A. Bratkowski, D. Bauman, R. Hertmanowski, *Institute of Physics, N. Copernicus University, Toruń, Poland*
- B 24 THE PHOTOLUMINESCENCE, OPTICAL TRANSMISSION AND REFLECTION OF Alq₃ LAYERS OBTAINED BY THERMAL EVAPORATION DEPOSITION** Paweł Dalasiński, Zbigniew Łukasiak, Mateusz Rebarz, Waclaw Bała, *Institute of Physics, UMK, Torun, Poland*
- B 25 TEMPERATURE DEPENDENT STUDY OF TRANSIENT PHOTOLUMINESCENCE AND PHOTOCONDUCTIVITY OF POROUS SILICON PREPARED BY ELECTROCHEMICAL ANODISATION** Zbigniew Łukasiak, Paweł Dalasiński, Artur Bratkowski, Waclaw Bała *Institute of Physics, N. Copernicus University, Torun, Poland*
- B 26 EFFECT OF HEAT TREATMENT AT ENHANCED PRESSURE ON ELECTRICAL AND STRUCTURAL PROPERTIES OF SILICON SURFACE LAYER CO-IMPLANTED WITH HYDROGEN AND HELIUM IONS** W. Jung, A. Misiuk, J. Ratajczak. *Institute of Electron Technology, Warsaw, Poland;*
- B 27 OPTICAL STUDIES OF DEFECTS GENERATED IN NEUTRON-IRRADIATED Cz-Si DURING HP-HT TREATMENT** B. Surma, A. Misiuk, A. Wnuk, A. Bukowski *Institute of Electronic Materials Technology, Warsaw, Poland*
- B 28 LATTICE PARAMETER MEASUREMENTS OF BORON DOPED Si SINGLE CRYSTALS** J. Kucytowski and K. Wokulska *Institute of Materials Science, University of Silesia, Katowice, Poland*
- B 29 NOVEL GAS SENSOR AND OPTICAL GAS SENSOR BASED ON POROUS SILICON MEASURED BY PHOTOVOLTAGE AND ADMITTANCE SPECTROSCOPY** A. Bratkowski, P. Borowski, W. Bała, A. Korcala, Z. Łukasiak *Institute of Physics, N. Copernicus University, Toruń, Poland*
- B 30 NOVEL APPROACH TO PREPARATION OF LEAD IODIDE FOR X-RAY DETECTION** M. Matuchová, O. Procházková, K. Ždánský, J. Zavadil, J. Maixner *Institute of Radio Engineering and Electronics, Academy of Sciences of the Czech Republic, Praha, Czech Republic*
- B 31 GROWTH AND PROPERTIES OF A₂MX₄ CRYSTALS** M. Suchańska, R. Belka, S. Kałuża *Department of Telecommunication and Photonics, Kielce University of Technology, Kielce, Poland;*
- B 32 TEM AND HREM CHARACTERISATION OF TiC CRYSTALS GROWN FROM HIGH TEMPERATURE Al SOLUTIONS** Z. Wokulski, D. Strzęciwilk and P. Tkacz *Institute of Materials Science, University of Silesia Katowice, Poland*
- B 33 MICROSTRUCTURAL CHARACTERIZATION OF CoSi₂ AND Co_{1-x}Ni_xSi₂ SINGLE CRYSTALS** Z. Wokulski, P. Stepniewski, W. Gurdziel and A. Kostka *Institute of Materials Science, University of Silesia Katowice, Poland*
- B 34 INFLUENCE OF DEFECT TRAPS AND INHOMOGENEITIES OF SiC CRYSTALS AND RADIATION DETECTORS ON CARRIER TRANSPORT** V. Kažukauskas, V. Kalendra, J.-V. Vaitkus *Semiconductor Physics Department, Institute of Materials Science and Applied Research of Vilnius University, Vilnius, Lithuania*
- B 35 DESIGN AND FABRICATION OF SEEDED SUBCRIPTION GROWTH SYSTEM FOR THE GROWTH OF SiC BOULES** G. Dhanaraj¹, M. Dudley, F. Liu, H. Zhang and V. Prasad *Dept. of Materials Science and Engineering State University of New York at Stony Brook, Stony Brook, USA*
- B 36 GROWTH AND OPTICAL CHARACTERIZATION OF Cd_{1-x}Be_xSe AND Cd_{1-x}Mg_xSe CRYSTALS** F. Firszt, S. Łęgowski, A. M. Marasek, H. Męczyńska, M. Pawlak, J. Zakrzewski A. A. Wronkowska, A. Wronkowski, W. Paszkowicz, *Institute of Physics, N. Copernicus University, Toruń, Poland.*
- B 37 INSTABILITY OF Al-Cu-Co SINGLE QUASICRYSTALS AT LOW TEMPERATURE** W. Bogdanowicz *Institute of Material Science, University of Silesia, Katowice, Bankowa, Poland*
- B 38 STUDY OF THE Al-Cu-Co SINGLE QUASICRYSTALS BY THE X-RAY TOPOGRAPHY METHOD** W. Bogdanowicz *Institute of Material Science, University of Silesia, 40-007 Katowice,*
- B 39 GROWTH COPPER SINGLE CRYSTALS OF VERY LARGE SIZE (Φ 140 MM) AND IMPROVEMENT THEIR NEUTRON REFLECTIVITY BY COLD HAMMERING PROCESS.** Stanisław Bednarski, Marek Chojnowski, Mariusz Wieczorkowski *Crystal Growth Laboratory Institute of Atomic Energy; Świerk-Otwock; Poland*
- B 40 EXPERIMENTAL INVESTIGATION OF THE ANISOTROPY OF QUADRATIC ELECTROOPTIC EFFECT IN ADP**
R. Ledzion, M. Izdebski, K. Bondarczuk, W. Kucharczyk, *Institute of Physics, Technical University of Łódź, Poland*
- B 41 ON THE REAL AND APPARENT FOURTH-ORDER ELECTROOPTIC EFFECT IN CRYSTALS** M. Izdebski, R. Ledzion, K. Bondarczuk, W. Kucharczyk, *Institute of Physics, Technical University of Łódź, Łódź, Poland*
- B 42 TEMPERATURE DEPENDENCE OF THE ELECTROOPTIC COEFFICIENT r₂₂ IN LiNbO₃** *Institute of Materials Science, University of Silesia Katowice, Poland*

- B 43 ON THE SYNTHESIS, SINGLE CRYSTAL GRWTH AND THERMODYNAMIC PROPERTIES OF SrNdAlO₄–CaNdAlO₄ SOLID SOLUTIONS** A. Novosselov, M. Ryumin, G. Pushkina¹, F. Spiridonov, G. Zimina, L. Komissarova, A. Pajczkowska
- B 44 ANOMALOUS PROPERTIES OF RARE EARTH DOUBLE TUNGSTATES** M.T. Borowiec, T. Zayranyk, A. Szewczyk, V.P. Dyakonov, A. Majchrowski, H. Szymczak, *Institute of Physics, Polish Academy of Sciences, Warsaw, Poland*
- B 45 BRIDGMAN-STOCKBARGER GROWTH AND XPS STUDY OF LiY_{1-x}Eu_xF₄ CRYSTALS** P. Maślankiewicz, J. Szade and Ph. Daniel *Institute of Physics, University of Silesia, Katowice, Poland*
- B46 BRIDGMAN GROWTH AND PROPERTIES OF KMgF₃ SINGLE CRYSTALS** P.V. Nefedov, N.I. Leonyuk *All-Russian Research Institute for Synthesis of Minerals (VNIISIMS)*
- B 47 FLUX CRYSTALLIZATION IN CONDITIONS OF ADJACENT PHASE'S COMPETITION** L.N. Bezmaternykh, V.L. Temerov, I.A. Gudim, N.A. Stolbovaja *L.V. Kirensky Institute of Physics, Krasnoyarsk, Russia*
- B 48 GENERATION-RECOMBINATION EFFECTS IN HIGH TEMPERATURE HgCdTe HETEROSTRUCTURE PHOTODIODES.** A. Jozwikowska, K. Jozwikowski, J. Rutkowski, A. Rogalski and Z. Orman *Warsaw Agricultural University, Warsaw, Poland.*
- B 49 HIGH-RESOLUTION PHOTOINDUCED TRANSIENT SPECTROSCOPY OF DEFECT CENTRES IN SEMI-INSULATING CdTe:Sn** P. Kaminski, R. Kozłowski, M. Miczuga, and I. Turkevych, *Institute of Electronic Materials Technology, Warszawa, Poland*
- B 50 SINGLE CRYSTAL PHASES IN THE Ga-Mg-Zn SYSTEM** Surowiec, M. Jeleń, P. *Institute of Material Science, University of Silesia, 40 007 Katowice, Bankowa 12, Poland*
- B 51 HIGH PRESSURE GROWTH AND PROPERTIES OF Mg_{1-x}Al_xB₂ SINGLE CRYSTALS** N. Zhigadlo, J. Karpinski, S. M. Kazakov, J. Jun, R. Puzniak, A. Wisniewski, *Solid State Physics Laboratory ETH, 8093 Zürich, Institute of Physics Polish Academy of Sciences, 02 668 Warsaw*
- B 52 GROWTH OF SINGLE CRYSTALS OF THE UTSb₂ COMPOUNDS** Zbigniew Bukowski *Polish Academy of Sciences, W. Trzebiatowski Institute of Low Temperature and Structure Research,*
- B 53 APPLICATION OF PIEZOELECTRIC MONOCRYSTALS IN DEVICES OF EXACT POSITIONING OF PROBE MICROSCOPES** V. Antipov, M. Malinkovich, Yu. Parkhomenko *Moscow Steel and Alloys Institute, Russia*
- B 54 A NITRIDE VCSEL WITH THE RADIAL BUILT-IN WAVEGUIDING MECHANISM** P. Maćkowiak, R. P. Sarzała, M. Wasiak, and W. Nakwaski *Laboratory of Computer Physics, Institute of Physics, Technical University of Łódź, Łódź, Poland*
- B55 PREPARATION AND CHARACTERIZATION OF PHOSPHORIC ACID-DOPED TRI-GLYCINE SULFATE CRYSTALS** E. M. El-Maghraby *Physics Department, Faculty of Science, Assiut University, Assiut 71516, Egypt*
- B 56 THE RAYLEIGH AND RAMAN SCATTERING IN CRYSTALLINE POLYOXYETHYLENEGLYCOLS** M. Mühle, M. Kozielski and Z. Błaszczak
- B 57 INVESTIGATION OF UREA INCLUSION COMPOUNDS BY BRILLOUIN SCATTERING** S. Mielcarek, T. Breczewski, B. Mroz, A. Trzaskowska, H. Bocanegra, L. Rubio-Pena *Faculty of Physics, A. Mickiewicz University, Poznań, Poland,*
- B 58 EXCITON ENERGIES AND PROPABILITIES OF THEIR RADIATIVE DECAY IN GaN/AlN QUANTUM STRUCTURES** T. Tchelidze, T. Kereselidze, *Tbilisi State University, Tbilisi, Georgia*